PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	Toshiharu Furukawa et al.	:	Date: January 29, 2004
Group Art Unit:	Unassigned	:	IBM Corporation
Examiner:	Unassigned	:	Intellectual Property Law
Serial No.:	Unassigned	:	Dept. 917, Bldg. 006-1
Filed:	Herewith	:	3605 Highway 52 North
Title:	VERTICAL NANOTUBE SEMICONDUCTOR DEVICE STRUCTURES AND METHODS OF FORMING THE SAME	:	Rochester, MN 55901-7829

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants request that the information listed on the attached Form PTO/SB/08A be considered by the Office during the pendency of the above entitled application, pursuant to 37 C.F.R. §1.97. In accordance with 37 C.F.R. §1.97(h), the filing of this Information Disclosure Statement shall not constitute an admission that any information cited therein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b). In the interest of full and complete disclosure to the Office, some or all of the art cited herein may not be considered by Applicant(s) or the Undersigned to be material under the new standard of materiality defined in 37 C.F.R. §1.56(b), enacted March 16, 1992, but may be material under the old standard of materiality defined in 37 C.F.R. §1.56(a), last amended on November 28, 1988, or may merely be technical background which may be of interest to the Examiner. In accordance with

37 C.F.R. §1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made.

This Information Disclosure Statement is being filed under 37 C.F.R. §1.97(b)(1) within three months of the filing date of the present application. Accordingly no filing fee is required.

Date: January 29, 2004

Respectfully submitted,

By _____

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 1 of 4

Application Number.:	Unassigned
Filing Date:	Herewith
First Named Inventor:	Toshiharu Furukawa
Art Unit:	Unassigned
Examiner Name:	Unassigned
Attorney Docket Number.:	ROC920030268US1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear
		US - 6,423,583 B1	07-23-2002	Avouris et al.	
		US - 6,515,325 B1	02-04-2003	Farnworth et al.	
		US - 2003/0168683 A1	09-11-2003	Farnworth et al.	
		US - 2003/0170930 A1	09-11-2003	Choi et al.	
		US - 2003/0178617 A1	09-25-2003	Appenzeller et al.	
		US -			
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FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.[1]	Foreign Patent Document Country[3] - Number[4] - Kind Code[5] (if known) Code	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear	T[6]

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[4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. [6] Applicant is to place a check mark here if English language translation is attached.

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and or country where published.	T[2]
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		B. ZHENG et al., "Efficient CVD Growth of Single-Walled Carbon Nanotubes on Surfaces Using Carbon Monoxide Precursor," Nano Letters, xxxx, Vol. 0., No. 0, A-D, xxxx American Chemical Society, received June 4, 2002, revised June 26, 2002.	
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		"IBM Scientists Develop Carbon Nanotube Transistor Technology," IBM.com News, news report concerning work published in Science, Vol. 292, Issue 5517, April 27, 2001 entitled "Engineering Carbon Nanotubes and Nanotube Circuits Using Electrical Breakdown" by Phaeton Avouris et al.	

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